# 2SA0794 (2SA794), 2SA0794A (2SA794A)

### Silicon PNP epitaxial planar type

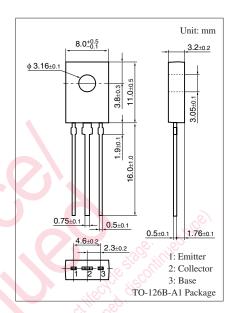
For low-frequency output driver Complementary to 2SC1567, 2SC1567A

#### ■ Features

- $\bullet$  High collector-emitter voltage (Base open)  $V_{\text{CEO}}$
- Optimum for the driver stage of low-frequency and 40 W to 100 W output amplifier
- TO-126B package which requires no insulation plate for installation to the heat sink

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter			Unit	
2SA0794	V <sub>CBO</sub>	-100	V	
2SA0794A		-120		
2SA0794	V <sub>CEO</sub>	-100	V	
2SA0794A		-120		
Emitter-base voltage (Collector open)			V	
Collector current			A	
Peak collector current			A	
Collector power dissipation			W	
Junction temperature			°C	
Storage temperature				
	2SA0794A 2SA0794 2SA0794A ector open)	Symbol   2SA0794   V <sub>CBO</sub>   2SA0794A     V <sub>CEO</sub>   2SA0794A     V <sub>CEO</sub>     V <sub>CEO</sub>     I <sub>C</sub>   I <sub>CP</sub>     I <sub>CP</sub>     I <sub>CP</sub>     I <sub>CP</sub>	2SA0794 V <sub>CBO</sub> -100 2SA0794A -120 2SA0794A V <sub>CEO</sub> -100 2SA0794A -120 lector open) V <sub>EBO</sub> -5 I <sub>C</sub> -0.5 I <sub>CP</sub> -1 In P <sub>C</sub> 1.2	



#### ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

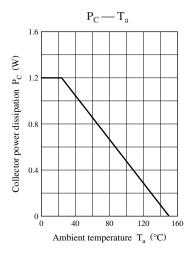
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SA0794	V <sub>CEO</sub>	$I_{\rm C} = -100 \mu\text{A},  I_{\rm B} = 0$	-100			V
(Base open)	2SA0794A	and s	into,	-120			
Emitter-base voltage (Colle	ctor open)	$V_{\rm EBO}$	$I_{\rm E} = -1  \mu A,  I_{\rm C} = 0$	-5			V
Forward current transfer ratio		h <sub>FE1</sub> *	$V_{CE} = -10 \text{ V}, I_{C} = -150 \text{ mA}$	90		220	_
		$h_{\rm FE2}$	$V_{CE} = -5 \text{ V}, I_{C} = -500 \text{ mA}$	50	100		
Collector-emitter saturation	voltage 👌	V <sub>CE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.2	- 0.4	V
Base-emitter saturation volt	tage	V <sub>BE(sat)</sub>	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		- 0.85	-1.20	V
Transition frequency	A	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		120		MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20	30	pF
(Common base, input open circuited)							

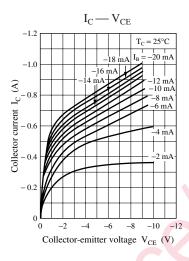
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

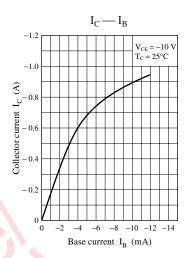
#### 2. \*: Rank classification

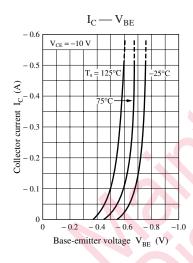
Rank	Q	R
h <sub>FE1</sub>	90 to 155	130 to 220

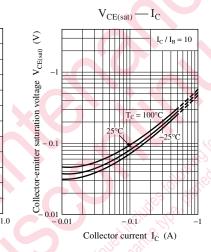
Note) The part numbers in the parenthesis show conventional part number.

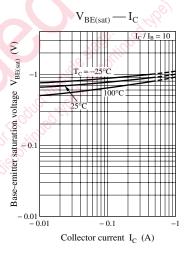


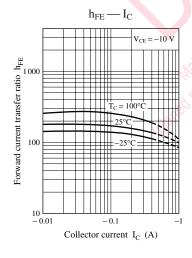


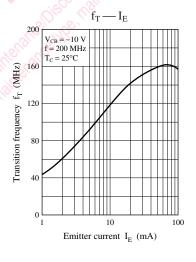


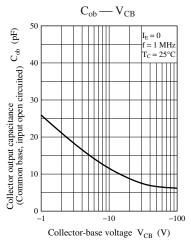


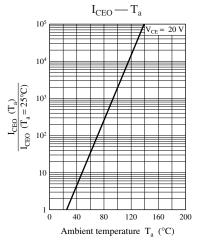


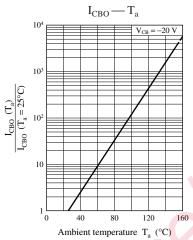


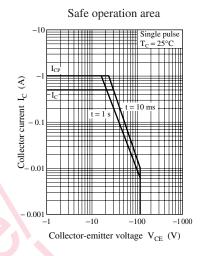












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